Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	811	@ad<="20030915" and (257/903). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:35
L2	324	@ad<="20030915" and (257/380-381).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:40
L3	138	@ad<="20030915" and (257/385). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:41
L4	260	@ad<="20030915" and (257/756). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:41
L5	501	@ad<="20030915" and (438/647). ccls. or (438/657).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:43
L7	196	@ad<="20030915" and (438/630). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:45
S1	9	@ad<="20030915" and 'cell' same 'logic' same 'cell gate oxide' and 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:03
S2	30	@ad<="20030915" and 'SRAM' same 'dual' with 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:40
S3	6963	@ad<="20030915" and (257/382). ccls. or (257/532).ccls. or (257/755).ccls. or (257/763).ccls. or (257/E21.507).ccls. or (257/E21. 59).ccls. or (257/E21.593).ccls. or (257/E21.66).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:38
S4	3125	@ad<="20030915" and (438/238). ccls. or (438/586).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:35
S5	1	"6080647".PN.	USPAT; USOCR	OR	ON	2004/12/06 16:19

S6	1	"5866451".PN.	USPAT; USOCR	OR	ON	2004/12/06 16:19
S7	5938	@ad<="20030915" and (438/621). ccls. or (438/655).ccls. or (438/656).ccls. or (438/657).ccls. or (438/253).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:29
S8	1	"6294420".PN.	USPAT; USOCR	OR	ON	2004/12/06 16:22
S9	1	"6177340".PN.	USPAT; USOCR	OR	ON	2004/12/06 16:22
S10	2030	@ad<="20030915" and (438/585). ccls. or (438/152).ccls. or (438/594).ccls. or (438/734).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:29
S12	159	@ad<="20030915" and 'SRAM' same 'polysilicon layers' and 'cell' and 'logic'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 17:21
S13	122	@ad<="20030915" and 'SRAM' same 'polysilicon layers' and 'cell' and 'peripheral'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:43
S14	2188	@ad<="20030915" and (438/253). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 17:03
S15	174	@ad<="20030915" and 'SRAM' same 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 17:22
S16	669	@ad<="20030915" and 'SRAM' and 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 17:22
S17	543	@ad<="20030915" and 'SRAM' and 'first polysilicon' and 'second polysilicon' and 'cell' and 'device'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 17:23
S18	304	@ad<="20030915" and 'SRAM' and 'first polysilicon' and 'second polysilicon' and 'cell' same 'device' same 'region'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 08:28

S19	653	@ad<="20030915" and 'SRAM' same 'memory' and 'peripheral' and 'polysilicon layers'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON ·	2004/12/07 08:29
S20	301	@ad<="20030915" and 'SRAM' and 'first polysilicon' and 'second polysilicon' and 'memory' same 'device' same 'region'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 08:29
S21	9	@ad<="20030915" and 'SRAM' same 'memory' same 'peripheral' same 'polysilicon layers'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 08:29